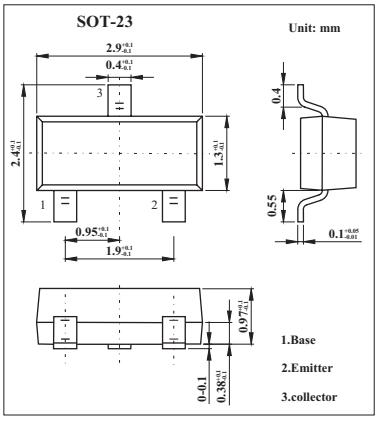
Silicon PNP Epitaxial Planar Type

2SB792,2SB792A



■ Features

- High collector-emitter voltage V_{CEO}
- Low noise voltage NV

■ Absolute Maximum Ratings Ta = 25℃

Parameter		Symbol	Rating	Unit
Collector-base voltage	2SB792	V_{CBO}	-150	V
	2SB792A		-185	V
Collector-emitter voltage	2SB792	V_{CEO}	-150	V
	2SB792A		-185	V
Emitter-base voltage		V_{EBO}	-5	V
Collector current		I_C	-50	mA
Peak collector current		I_{CP}	-100	mA
Collector power dissipation		P_C	200	mW
Junction temperature		T_j	150	℃
Storage temperature		T_{stg}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter		Symbol	Testconditons	Min	Typ	Max	Unit
Collector-emitter voltage	2SB792	V_{CEO}	I_C = -100 μA, I_B = 0	-150			V
	2SB792A			-185			V
Emitter-base voltage		V_{EBO}	I_E = -10 μA, I_C = 0	-5			V
Collector-base cutoff current		I_{CBO}	V_{CB} = -100 V, I_E = 0			-1	μA
Forward current transfer ratio	2SB792	h_{FE}	V_{CE} = -5 V, I_C = -10 mA	130		450	
	2SB792A			130		330	
Collector-emitter saturation voltage		$V_{CE(sat)}$	I_C = -30 mA, I_B = -3 mA			-1	V
Transition frequency		f_T	V_{CE} = -10 V, I_C = -10 mA, f = 200 MHz		200		MHz
Collector output capacitance		C_{ob}	V_{CB} = -10 V, I_E = 0, f = 1 MHz		4		pF
Noise voltage		NV	V_{CE} = -10 V, I_C = -1 mA, G_V = 80 dB Rg = 100KΩ, Function = FLAT		150		mV

■ h_{FE} Classification

Marking	2SB792	IR	IS	IT
	2SB792A	2FR	2FS	
Rank		R	S	T
h_{FE}		130～220	185～330	260～450